

HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS



DESCRIPTION

The IS357 is an optically coupled isolator consisting of an infrared light emitting diode and NPN silicon photo transistor in a space efficient dual in line plastic package.

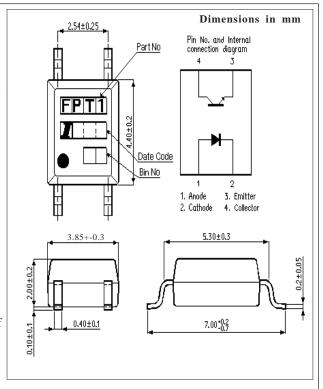
FEATURES

- Marked as FPT1.
- Current Transfer Ratio MIN. 50%
- Isolation Voltage $(3.75kV_{RMS}, 5.3kV_{PK})$
- All electrical parameters 100% tested
- Drop in replacement for Sharp PC357

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and

impedances



ISOCOMCOMPONENTSLTD

Unit 25B, Park View Road West, Park View Industrial Estate, Brenda Road Hartlepool, Cleveland, TS25 1UD Tel: (01429) 863609 Fax: (01429) 863581

27/11/08 DB92845

ABSOLUTEMAXIMUMRATINGS (25°C unless otherwise specified)

Storage Temperature	$_{-55^{\circ}\text{C}}$ to $+150^{\circ}\text{C}$
Operating Temperature	$_{-}$ -55°C to + 100°C
Lead Soldering Temperature	
(1/16 inch (1.6mm) from case for	10 secs) 260°C

INPUTDIODE

Forward Current	50mA	
Reverse Voltage	6V	
Power Dissipation	70mW	

OUTPUTTRANSISTOR

Collector-emitter Voltage BV _{CEO}	35V
Emitter-collector Voltage BV _{ECO}	6V
Collector Current	50mA
Power Dissipation	150mW

POWERDISSIPATION

Total Power Dissipation	170mW
(derate linearly 2.26mW/°C above 25°C)	

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ Unless otherwise noted)

	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.4	V	$I_F = 20 \text{mA}$
	Reverse Current (I_R)			10	μΑ	$V_{_{ m R}}$ =4 V
Output	$Collector-emitter Breakdown (BV_{CEO})$	35			V	$I_{\rm C}$ =0.5mA
	$\begin{aligned} & Emitter-collector Breakdown (BV_{ECO}) \\ & Collector-emitter Dark Current (I_{CEO}) \end{aligned}$	6		100	V nA	$I_{\rm E} = 0.1 \rm mA$ $V_{\rm CE} = 20 \rm V$
Coupled	Current Transfer Ratio (CTR)	50		600	%	$5\text{mAI}_{\text{F}}, 5\text{VV}_{\text{CE}}$
	Optional CTR Grades: IS357A IS357B IS357C IS357D	80 130 200 300		160 260 400 600	% % % %	$5\text{mAI}_{\text{F}}, 5\text{VV}_{\text{CE}}$ $5\text{mAI}_{\text{F}}, 5\text{VV}_{\text{CE}}$ $5\text{mAI}_{\text{F}}, 5\text{VV}_{\text{CE}}$ $5\text{mAI}_{\text{F}}, 5\text{VV}_{\text{CE}}$
	$\label{eq:Collector-emitterSaturationVoltageV} Collector-emitterSaturation Voltage V_{CE(SAT)}$ Input to Output Isolation Voltage $V_{\rm ISO}$	3750 5300		0.2	$egin{array}{c} V & & & & & & & & & & & & & & & & & & $	$20\text{mA I}_{\text{F}}, 1.0\text{mA I}_{\text{C}}$ See note 1 See note 1
	$\begin{array}{lll} \text{Input-output Isolation Resistance R}_{\text{ISO}} \\ \text{Output Rise Time} & \text{tr} \\ \text{Output Fall Time} & \text{tf} \\ \end{array}$	5x10 ¹⁰	4 3	18 18	Ω μs μs	$V_{IO} = 500V \text{ (note 1)}$ $V_{CE} = 2V,$ $I_{C} = 2mA, R_{L} = 100\Omega$

Note 1 Measured with input leads shorted together and output leads shorted together.

27/11/08 DB92845